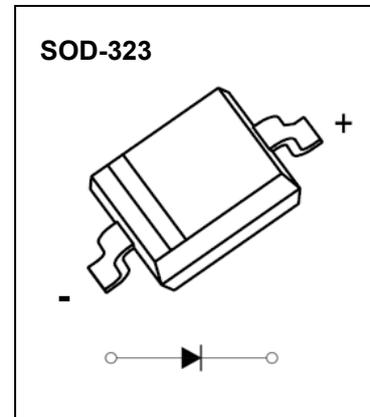


SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING:SD



Maximum Ratings @Ta=25°C

Parameter	Symbo	Value	Unit
Peak repetitive peak reverse voltage	V_{RRM}	20	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS reverse voltage reverse voltage (DC)	$V_{R(RMS)}$	14	V
Average rectified output current	I_o	0.5	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	5.5	A
Power dissipation	P_D	200	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	500	°C/W
Operating Junction Temperature Range	T_j	-40 ~ +125	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C
Voltage rate of change	dv/dt	1000	V/μs

Electrical Characteristics @Ta=25°C

	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=250\mu A$	20			V
Reverse current	I_R	$V_R=10V$			75	μA
		$V_R=20V$			250	
Forward voltage	V_F	$I_F=0.1A$			0.33	V
		$I_F=0.5A$			0.44	
Capacitance between terminals	C_T	$V_R=1, f=1MHz$		170		pF

Typical Characteristics

